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0229212.6 14 December 2002 (14.12.2002) GB(71) Applicant (for all designated States except US): KONIN-
KLJKE PHILIPS ELECTRONICS N.V. [NL/NL];
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventor; and

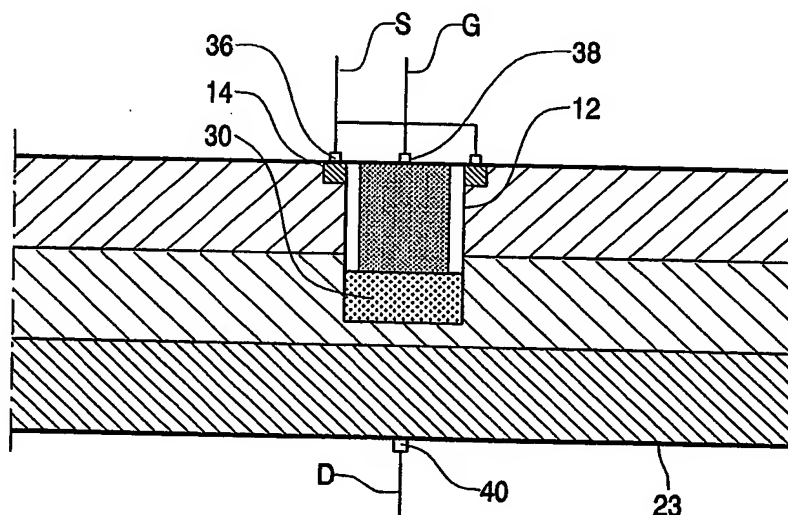
(75) Inventor/Applicant (for US only): HIJZEN, Erwin, A.
[NL/BE]; c/o Philips Intellectual Property & Standards,
Cross Oak Lane, Redhill, Surrey RH1 5HA (GB).(74) Agent: SHARROCK, Daniel, J.; Philips Intellectual
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(54) Title: METHOD OF MANUFACTURE OF A TRENCH-GATE SEMICONDUCTOR DEVICE



(57) Abstract: A method of making a trench MOSFET includes forming a layer of porous silicon (26) at the bottom of a trench and then oxidizing the layer of porous silicon (26) to form a plug (30) at the bottom of the trench. This forms a thick oxide plug at the bottom of the trench thereby reducing capacitance between gate and drain.

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